

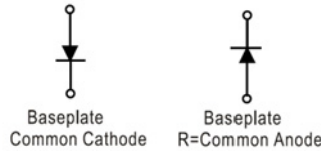
## Low $V_F$ Silicon Power Schottky Diode

$V_{RRM} = 30\text{ V}$   
 $I_{F(AV)} = 200\text{ A}$

### Features

- High Surge Capability
- Type 30 V  $V_{RRM}$
- Not ESD Sensitive

D-67 Package



### Maximum ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBRH20030(R)L	Unit
Maximum recurrent peak reverse voltage	$V_{RRM}$		30	V
Maximum RMS voltage	$V_{RMS}$		21	V
Maximum DC blocking voltage	$V_{DC}$		30	V
Operating temperature	$T_j$		-55 to 150	°C
Storage temperature	$T_{stg}$		-55 to 150	°C

### Electrical characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	MBRH20030(R)L	Unit
Average forward current	$I_{F(AV)}$	$T_C = 100\text{ °C}$	200	A
Peak forward surge current	$I_{FSM}$	$t_p = 8.3\text{ ms}$ , half sine	3000	A
Maximum instantaneous forward voltage	$V_F$	$I_{FM} = 200\text{ A}$ , $T_j = 25\text{ °C}$	0.58	V
Maximum instantaneous reverse current at rated DC blocking voltage	$I_R$	$T_j = 25\text{ °C}$	3	mA
		$T_j = 100\text{ °C}$	150	

### Thermal characteristics

Maximum thermal resistance, junction - case	$R_{\theta JC}$		0.35	°C/W
---	-----------------	--	------	------

Figure .1-Typical Forward Characteristics

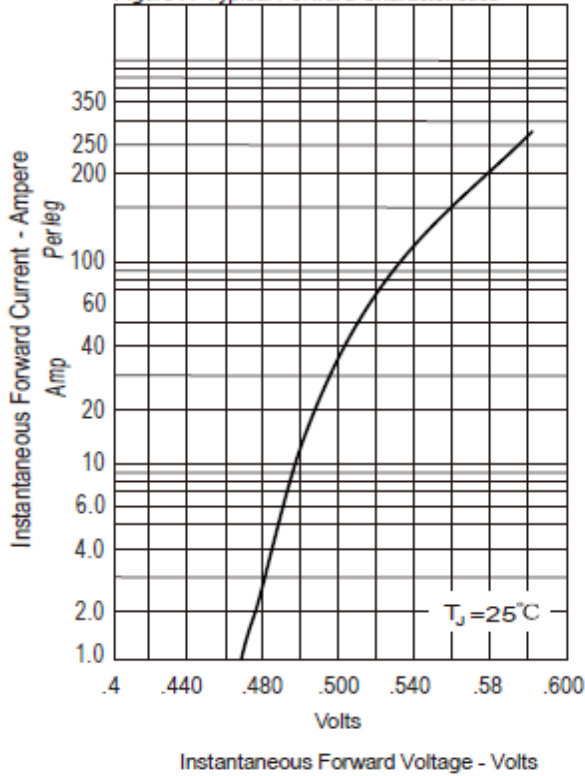


Figure .2- Forward Derating Curve

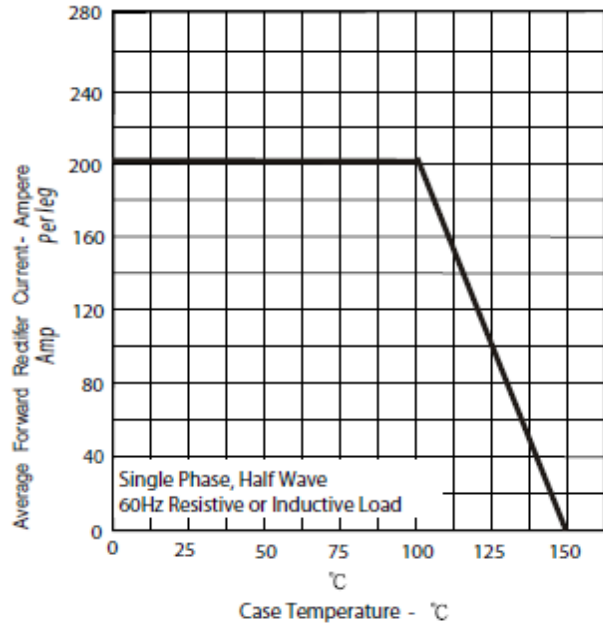


Figure.3-Peak Forward Surge Current

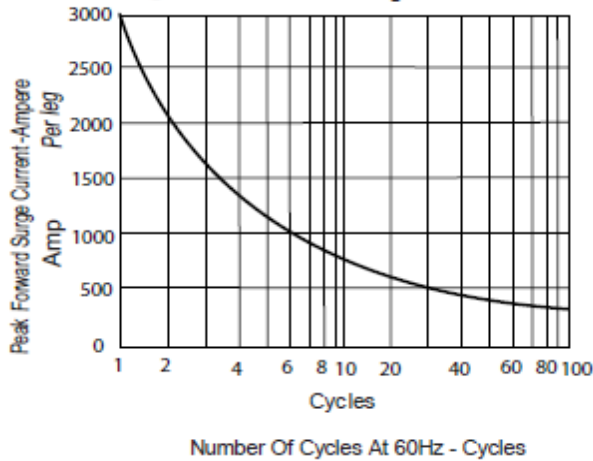
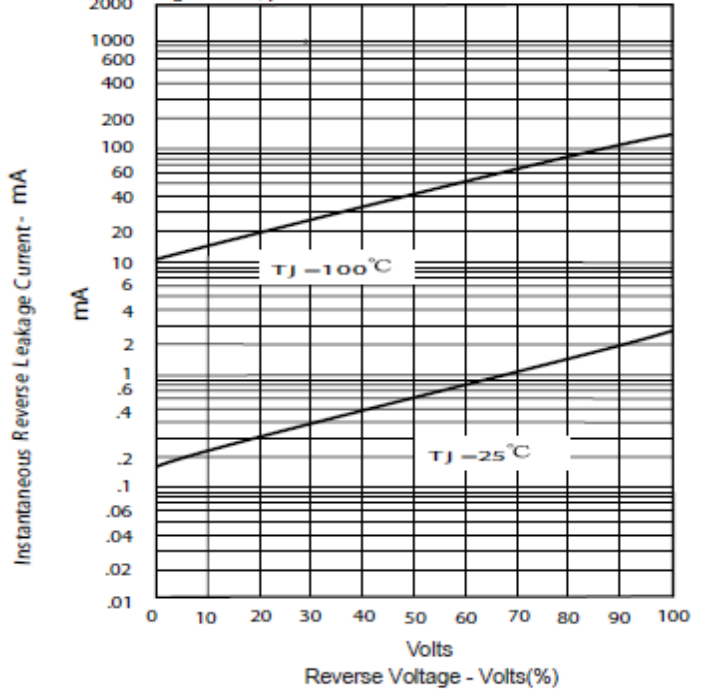
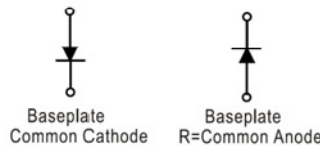
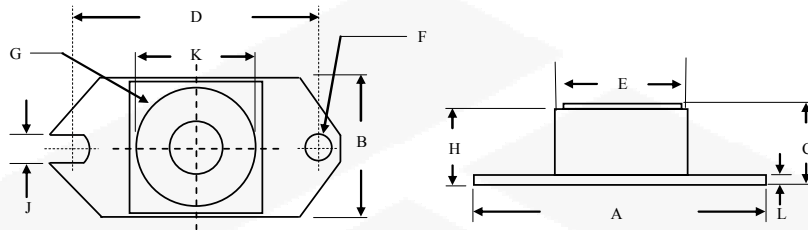


Figure .4-Typical Reverse Characteristics



**Package dimensions and terminal configuration**

Product is marked with part number and terminal configuration.



	Inches		Millimeters	
	Min	Max	Min	Max
A	1.515	1.560	38.48	39.62
B	0.725	0.775	18.42	19.69
C	0.595	0.625	15.11	15.88
D	1.182	1.192	30.02	30.28
E	0.736	0.744	18.70	18.90
F	0.152	0.160	3.86	4.061
G	1/4-20 UNC			
H	0.540	0.580	13.72	14.73
J	0.156	0.160	3.96	4.06
K	0.480	0.492	12.20	12.50
L	0.120	0.130	3.05	3.30